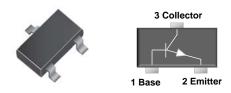


Small Signal Transistor



Features

- ♦Epitaxial planar die construction
- ♦Surface device type mounting
- ♦Moisture sensitivity level 1
- ♦ Matte Tin(Sn) lead finish with Nickel(Ni) underplate
- ♦Pb free version and RoHS compliant

Mechanical Data

- →Terminal: Matte tin plated, lead free., solderable per MIL-STD-202, Method 208 guaranteed
- ♦ High temperature soldering guaranteed: 260°C/10s
- ♦Weight : 0.008gram (approximately)

Ordering Information

Package	Part No.	Packing	Marking
SOT-23	BC846A RF	3K / 7" Reel	1A
SOT-23	BC846B RF	3K / 7" Reel	1B
SOT-23	BC847A RF	3K / 7" Reel	1E
SOT-23	BC847B RF	3K / 7" Reel	1F
SOT-23	BC847C RF	3K / 7" Reel	1G
SOT-23	BC848A RF	3K / 7" Reel	1J
SOT-23	BC848B RF	3K / 7" Reel	1K
SOT-23	BC848C RF	3K / 7" Reel	1L
SOT-23	BC846A RFG	3K / 7" Reel	1A
SOT-23	BC846B RFG	3K / 7" Reel	1B
SOT-23	BC847A RFG	3K / 7" Reel	1E
SOT-23	BC847B RFG	3K / 7" Reel	1F
SOT-23	BC847C RFG	3K / 7" Reel	1G
SOT-23	BC848A RFG	3K / 7" Reel	1J
SOT-23	BC848B RFG	3K / 7" Reel	1K
SOT-23	BC848C RFG	3K / 7" Reel	1L

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

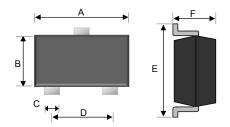
Maximum Ratings

Maximum Katings						
Type Number Power Dissipation		Value				
		250	mW			
BC846		80				
BC847	V _{CBO}	50	V			
BC848		30				
BC846		65				
BC847	V _{CEO}	45	V			
BC848		30				
BC846		6				
BC847	V _{EBO}	6	V			
BC848		5				
	lc	0.1	Α			
Junction and Storage Temperature Range		-55 to + 150	°C			
	BC847 BC848 BC846 BC847 BC848 BC846 BC847 BC848	BC847 VCBO BC848 BC846 BC847 VCEO BC848 BC846 BC846 BC846 BC847 BC848 BC847	PD 250 BC846 BC847 VCB0 50 BC848 BC846 BC847 VCE0 45 BC848 BC847 BC848 BC846 BC847 BC848 BC846 BC847 VEB0 6 BC847 BC848 Ic 0.1			

Notes:1. Valid provided that electrodes are kept at ambient temperature

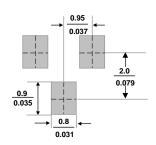
BC846A/B, BC847A/B/C, BC848A/B/C 250mW, NPN Small Signal Transistor

SOT-23



Dimensions	Unit	(mm)	Unit (inch)		
Dimensions	Min	Max	Min	Max	
Α	2.80	3.00	0.110	0.118	
В	1.20	1.40	0.047	0.055	
С	0.30	0.50	0.012	0.020	
D	1.80	2.00	0.071	0.079	
E	2.25	2.55	0.089	0.100	
F	0.90	1.20	0.035	0.043	

Suggested PAD Layout



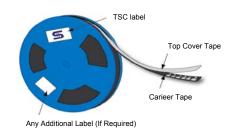


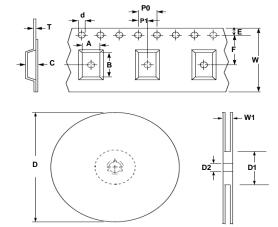
Small Signal Transistor

Electrical Characteristics

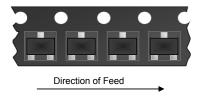
Type Number					Symbol	Min	Max	Units
Collector-Base Bre	akdown Voltage	BC846 BC847 BC848	I _C = 10μA	I _E = 0	V _{(BR)CBO}	80 50 30	-	V
Collector-Emitter B	reakdown Voltage	BC846 BC847 BC848	I _C = 10mA	I _B = 0	V _{(BR)CEO}	65 45 30	-	V
Emitter-Base Break	kdown Voltage	BC846 BC847 BC848	I _E = 1μA	I _C = 0	V _{(BR)EBO}	6 6 5	-	V
Collector Cut-off Cu	urrent		V _{CB} = 30V	I _E = 0	I _{CBO}	-	15	nA
Emitter Cut-off Cur	rent		V _{EB} = 5V	I _C =0	I _{EBO}	-	0.1	μA
DC current gain	BC846A, BC847A BC846B, BC847E BC847C, BC848C	B, BC848B	V _{CE} = 5V	I _C = 2mA	h _{FE}	110 200 420	220 450 800	
Collector-Emitter saturation voltage			I _C = 100mA	I _B = 5mA	V _{CE(sat)}	-	0.5	V
Base-Emitter saturation voltage		I _C = 100mA	I _B = 5mA	V _{BE(sat)}	-	1.1	V	
Transition frequency V _{CE} = 5V		I _C = 10mA	f= 100MHz	f _T	100	-	MHz	

Tape & Reel specification





Item	Symbol	Dimension(mm)		
Carrier width	Α	3.15 ±0.10		
Carrier length	В	2.77 ±0.10		
Carrier depth	С	1.22 ±0.10		
Sprocket hole	d	1.50 ± 0.10		
Reel outside diameter	D	178 ± 1		
Reel inner diameter	D1	55 Min		
Feed hole width	D2	13.0 ± 0.20		
Sprocke hole position	E	1.75 ±0.10		
Punch hole position	F	3.50 ±0.05		
Sprocke hole pitch	P0	4.00 ±0.10		
Embossment center	P1	2.00 ±0.05		
Overall tape thickness	T	0.229 ±0.013		
Tape width	W	8.10 ±0.20		
Reel width	W1	12.30 ±0.20		



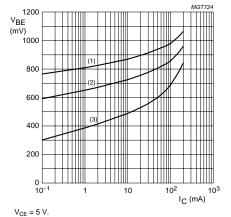


Small Signal Transistor

Rating and Characteristic Curves

Figure 1. Static Characteristic _ I_B = 350μA [mA], COLLECTOR CURRENT I_B = 300μA - I_B = 250μΑ $I_{R} = 200 \mu A$ I₀ = 150μΑ = 100µA = 50µA $V_{CE}[V]$, COLLECTOR-EMITTER VOLTAGE

Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage





⁽²⁾ $T_{amb} = 25 \,^{\circ}C$.

Figure 5. Collector Output Capacitance

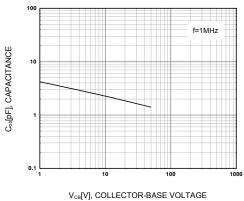
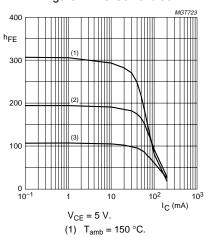


Figure 2. DC Current Gain



- (2) $T_{amb} = 25 \,^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Figure 4. Base-Emitter On Voltage

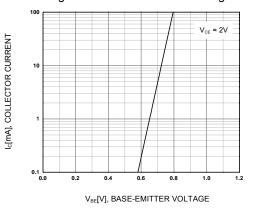
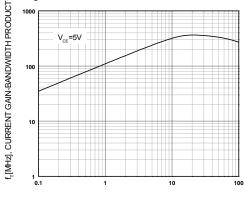


Figure 6. Current Gain Bandwidth Product



 $I_{c}[mA]$, COLLECTOR CURRENT

⁽³⁾ T_{amb} = 150 °C.